

INFORMATION DISCLOSURE CITATION PTO-1449			Atty. Docket No. NTI-703CIP3 Applicant PANG, Linyong Filing Date 7/11/03		Serial No. 19 618 816 Group 2825	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
VS	4,812,962	3/14/1989	Witt	364	490	4/9/1987
	5,051,598	9/24/1991	Ashton, et al.	250	492.2	9/12/1990
	5,182,718	1/26/1993	Harafuji, et al.	364	490	3/29/1990
	5,241,185	8/31/1993	Meiri, et al.	250	492.2	1/8/1992
	5,242,770	9/7/1993	Chen, et al.	430	5	1/16/1992
	5,256,505	10/26/1993	Chen, et al.	430	5	8/21/1992
	5,282,140	1/25/1994	Tazawa, et al.	364	468	6/24/1992
	5,316,878	5/31/1994	Saito, et al.	430	5	6/4/1992
	5,326,659	7/5/1994	Liu, et al.	430	5	3/5/1992
	5,340,700	8/23/1994	Chen, et al.	430	312	11/3/1993
	5,424,154	6/13/1995	Borodovsky	430	5	12/10/1993
	5,432,714	7/11/1995	Chung, et al.	364	525	9/2/1994
	5,447,810	9/5/1995	Chen, et al.	430	5	2/9/1994
	5,532,090	7/2/1996	Borodovsky	430	5	3/1/1995
	5,533,148	7/2/1996	Sayah, et al.	382	240	9/30/1993
	5,538,815	7/23/1996	Oi, et al.	430	5	9/14/1993
	5,553,273	9/3/1996	Liebmann	395	500	4/17/1995
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	5,572,598	11/5/1996	Wihl, et al.	382	144	2/25/1994
	5,631,110	5/20/1997	Shioiri, et al.	430	5	6/5/1995
	5,657,235	8/12/1997	Liebmann, et al.	364	474.24	5/3/1995
	5,663,017	9/2/1997	Schinella, et al.	430	5	6/7/1995
VS	5,663,893	9/2/1997	Wampler, et al.	364	491	5/3/1995

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VS	5,702,848	12/30/1997	Spence	430	5	8/23/1996
	5,705,301	1/6/1998	Garza, et al.	430	5	2/27/1996
	5,707,765	1/13/1998	Chen	430	5	5/28/1996
	5,740,068	4/14/1998	Liebmann, et al.	364	489	5/30/1996
	5,795,688	8/18/1998	Burdorf, et al.	430	30	8/14/1996
	5,801,954	9/1/1998	Le, et al.	364	488	4/24/1996
	5,804,340	9/8/1998	Garza, et al.	430	5	12/23/1996
	5,815,685	9/29/1998	Kamon	395	500	9/15/1995
	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
	5,827,623	10/27/1998	Ishida, et al.	430	5	10/30/1996
	5,847,959	12/8/1998	Veneklasen, et al.	364	468.28	1/28/1997
	5,849,440	12/15/1998	Lucase, et al.	430	5	1/29/1997
	5,862,058	1/19/1999	Samuels, et al.	364	491	5/16/1996
	5,863,682	1/26/1999	Abe, et al.	430	30	2/21/1997
	5,879,844	3/9/1999	Yamamoto, et al.	430	30	12/20/1996
	5,900,338	5/4/1999	Garza, et al.	430	5	8/15/1997
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	5,972,541	10/26/1999	Sugasawara, et al.	430	5	3/4/1998
	6,009,250	12/28/1999	Ho, et al.	395	500.06	9/30/1997
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	6,011,911	1/4/2000	Ho, et al.	395	500.06	9/30/1997
	6,016,357	1/18/2000	Neary, et al.	382	144	6/16/1997
VS	6,076,465	6/20/2000	Vacca, et al.	101	481	9/19/1997

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
VS	6,077,310	6/20/2000	Yamamoto, et al.	716	19	1/29/1999
	6,078,738	6/20/2000	Garza, et al.	395	500.22	5/8/1997
	6,081,658	6/27/2000	Rieger, et al.	395	500.22	12/31/1997
	6,081,659	6/27/2000	Garza, et al.	395	500.22	4/26/1999
	6,130,750	10/10/2000	Ausschnitt, et al.	356	401	8/28/1997
	6,171,731 B1	1/9/2001	Medvedeva, et al.	430	5	1/20/1999
	6,185,727 B1	2/6/2001	Liebmann	716	19	12/12/1995
	2002/0019729 A1	2/14/2002	Chang, et al.	703	6	8/7/1998
VS	2002/0035461 A1	3/21/2002	Chang, et al.	703	13	7/16/2001

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		Filing Date					
FOREIGN PATENT DOCUMENTS							
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	WO 97/38381 A1 ✓	10/16/1997	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 98/20327 A1 ✓	5/14/1998	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 98/45685 A1 ✓	10/15/1998	WO			<input type="checkbox"/>	<input type="checkbox"/>
VS	WO 99/14706 A2/A3 ✓	3/25/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
EXAMINER'S INITIALS	CITATION		
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	Microunity, "OPC Technology & Product Description", MicroUnity Systems Engineering, Inc., pp. 1-5.		
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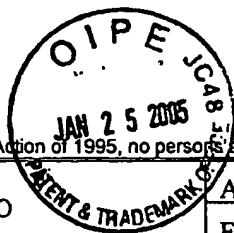
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				Filing Date		7/11/2003		
				First Named Inventor:		Linyong Pang		
				Examiner: Unknown		GROUP: 2825		
Sheet		1 of 1		Attorney Docket Number		NTI-703-1P1P		
U.S. PATENT DOCUMENTS								
Examiner Initials*	Cited No. ¹	Document Number Number - Kind Code ² (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document		Pages, Columns, Lines Where Relevant Passages or Figures Appear	
IS	A01	US-5,504,335		04/02/1996	Maarschalkerweerd			
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